

MICROWAVE POWER GaAs FET

TIM7785-25UL

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 44.5dBm at 7.7GHz to 8.5GHz

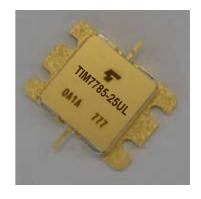
·HIGH GAIN

G1dB= 8.5dB at 7.7GHz to 8.5GHz

LOW INTERMODULATION DISTORTION

IM3(MIN.) = -44dBc at Pout= 33.5dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 5.2A f= 7.7 to 8.5GHz	dBm	43.5	44.5	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	7.5	8.5	_
Drain Current	IDS1		Α	_	6.8	7.6
Gain Flatness	ΔG		dB	_	_	±0.6
Power Added Efficiency	ηadd		%	_	36	_
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 33.5dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-44	-47	_
Drain Current	IDS2		Α	_	5.2	6.0
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C	_	_	80

Recommended Gate Resistance (Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 8.0A	S	_	5.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 80mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	Α	_	14.4	_
Gate-Source Breakdown Voltage	VGSO	IGS= -280 _μ A	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.2	1.5

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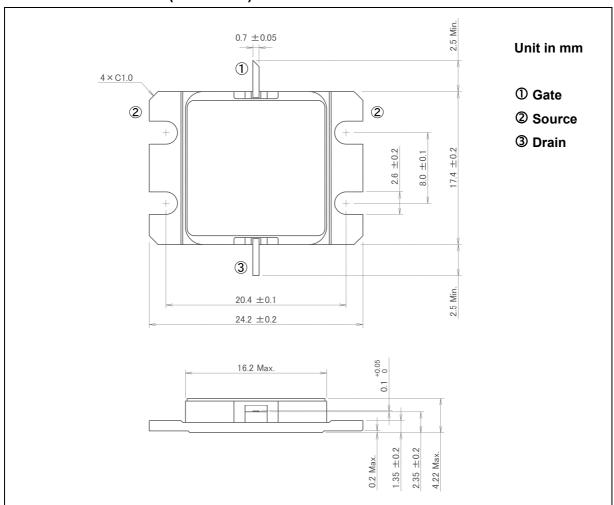
- MICROWAVE SEMICONDUCTOR TECHNICAL DATA



ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	20.0
Total Power Dissipation (Tc= 25°C)	PT	W	100
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-16G1B)



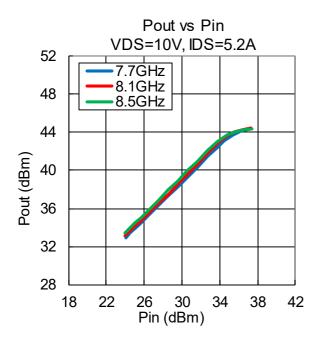
HANDLING PRECAUTIONS FOR PACKAGE MODEL

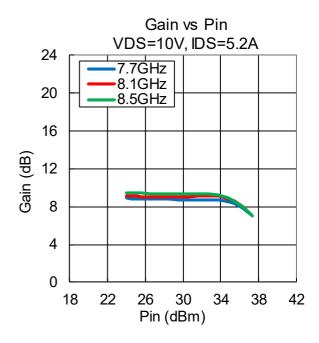
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

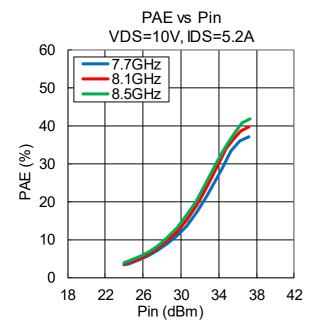
TYPICAL RF PERFORMANCE

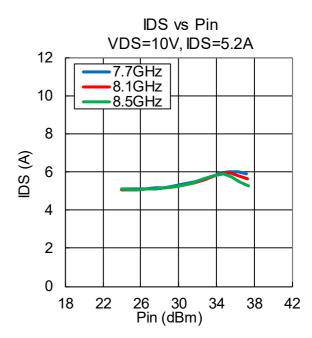
·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 5.2 A, f= 7.7, 8.1, 8.5 GHz, Ta= +25 °C



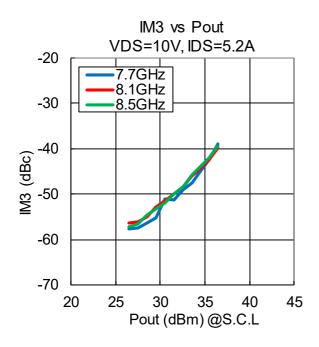


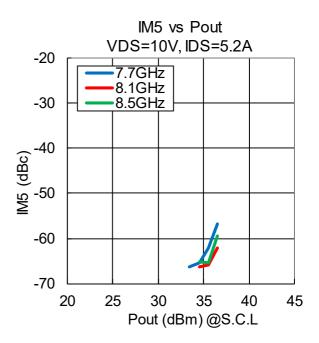




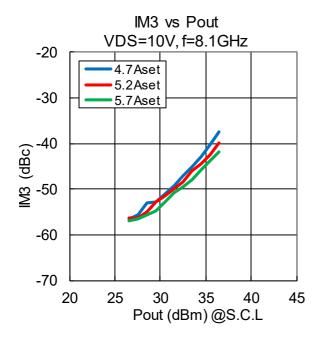
·IM3, IM5 vs. Pout

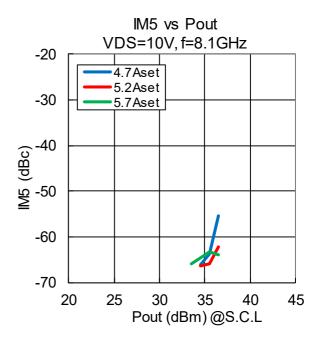
VDS= 10 V, IDSset= 5.2 A, f= 7.7, 8.1, 8.5 GHz, Δf = 5 MHz , Ta= +25 $\,^{\circ}\mathrm{C}$





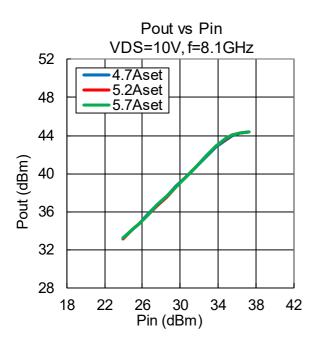
VDS= 10 V, IDSset= 4.7, 5.2, 5.7 A, f= 8.1 GHz, Δ f= 5 MHz , Ta= +25 $^{\circ}$ C

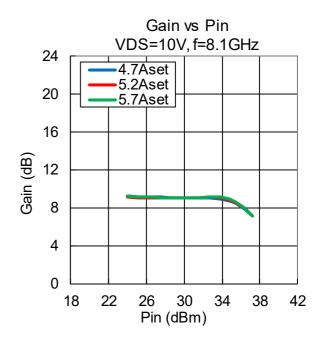


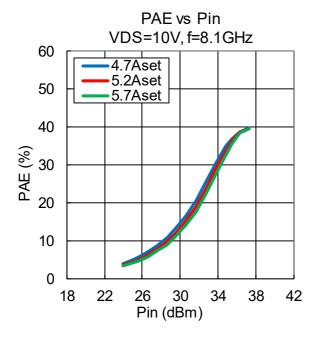


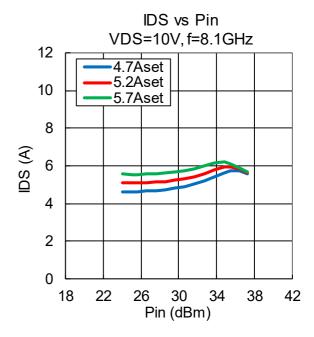
·Pout , Gain , PAE , IDS vs. Pin vs. IDSset

VDS= 10 V, IDSset= 4.7, 5.2, 5.7 A, f= 8.1 GHz, Ta= +25 °C





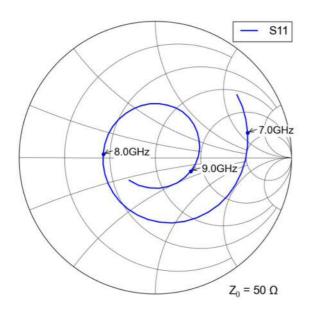


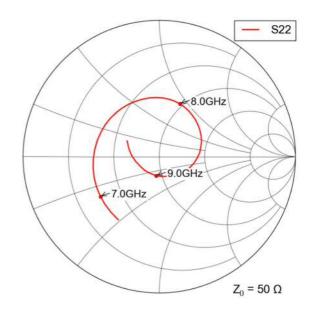


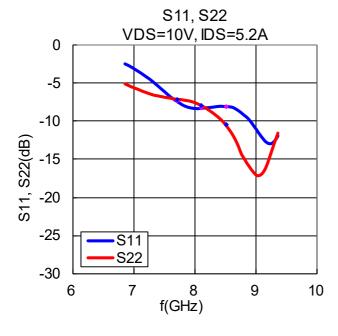


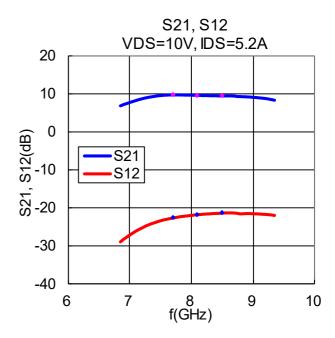
·S-Parameters

VDS= 10 V, IDSset= 5.2 A, f= 6.85 to 9.35 GHz, Ta= +25 $^{\circ}$ C











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